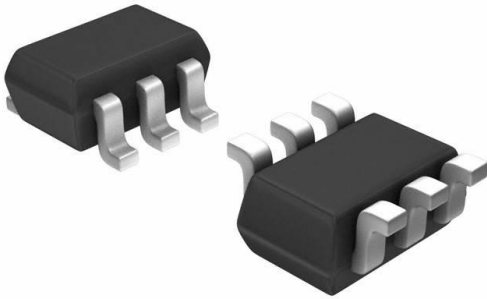


BC856BDW1T1 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	BC856BDW1T1-DG
Manufacturer	onsemi
Manufacturer Product Number	BC856BDW1T1
Description	TRANS 2PNP 65V 0.1A SOT363
Detailed Description	Bipolar (BJT) Transistor Array 2 PNP (Dual) 65V 100mA 100MHz 380mW Surface Mount SC-88/SC70-6/SO T-363



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

BC856BDW1T1

Series:

-

Transistor Type:

2 PNP (Dual)

Voltage - Collector Emitter Breakdown (Max):

65V

Current - Collector Cutoff (Max):

15nA (ICBO)

Power - Max:

380mW

Operating Temperature:

-55°C ~ 150°C (TJ)

Package / Case:

6-TSSOP, SC-88, SOT-363

Base Product Number:

BC856

Manufacturer:

onsemi

Product Status:

Obsolete

Current - Collector (Ic) (Max):

100mA

Vce Saturation (Max) @ Ib, Ic:

650mV @ 5mA, 100mA

DC Current Gain (hFE) (Min) @ Ic, Vce:

220 @ 2mA, 5V

Frequency - Transition:

100MHz

Mounting Type:

Surface Mount

Supplier Device Package:

SC-88/SC70-6/SOT-363

Environmental & Export classification

RoHS Status:

RoHS non-compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

BC856BDW1T1, BC857BDW1T1 Series, BC858CDW1T1 Series

Preferred Devices

Dual General Purpose Transistors

PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-65 -45 -30	V
Collector-Base Voltage	V_{CBO}	-80 -50 -30	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current -Continuous	I_C	-100	mAdc

THERMAL CHARACTERISTICS

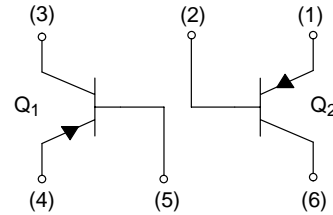
Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	380 250 3.0	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	328	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in



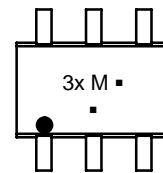
ON Semiconductor®

<http://onsemi.com>


1

SOT-363/SC-88
CASE 419B
STYLE 1

MARKING DIAGRAM



3x = Specific Device Code
x = B, F, G, or L
(See Ordering Information)
M = Date Code
■ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

BC856BDW1T1, BC857BDW1T1 Series, BC858CDW1T1 Series**ELECTRICAL CHARACTERISTICS** ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ mA}$)	$V_{(BR)CEO}$	-65 -45 -30	-	-	V
Collector–Emitter Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $V_{EB} = 0$)	$V_{(BR)CES}$	-80 -50 -30	-	-	V
Collector–Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$)	$V_{(BR)CBO}$	-80 -50 -30	-	-	V
Emitter–Base Breakdown Voltage ($I_E = -1.0\text{ }\mu\text{A}$)	$V_{(BR)EBO}$	-5.0 -5.0 -5.0	-	-	V
Collector Cutoff Current ($V_{CB} = -30\text{ V}$) ($V_{CB} = -30\text{ V}$, $T_A = 150^\circ\text{C}$)	I_{CBO}	-	-	-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain ($I_C = -10\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$)	h_{FE}	-	150	-	-
($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$)		220 420	290 520	475 800	
Collector–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{CE(sat)}$	-	-	-0.3 -0.65	V
Base–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) ($I_C = -100\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{BE(sat)}$	-	-0.7 -0.9	-	V
Base–Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ V}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ V}$)	$V_{BE(on)}$	-0.6 -	-	-0.75 -0.82	V
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	-	-	MHz
Output Capacitance ($V_{CB} = -10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{ob}	-	-	4.5	pF
Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF	-	-	10	dB

BC856BDW1T1, BC857BDW1T1 Series, BC858CDW1T1 Series

TYPICAL CHARACTERISTICS – BC856

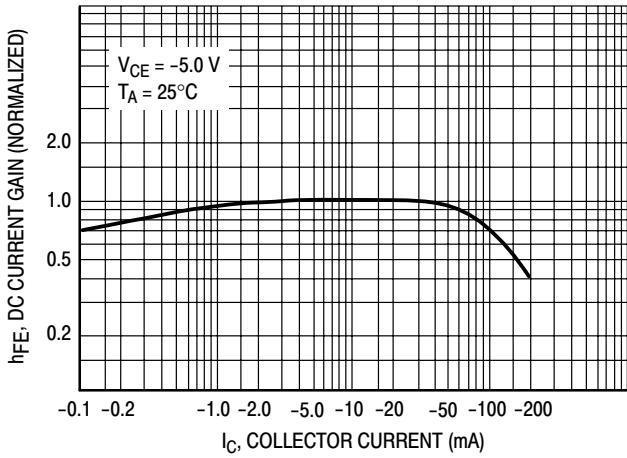


Figure 1. DC Current Gain

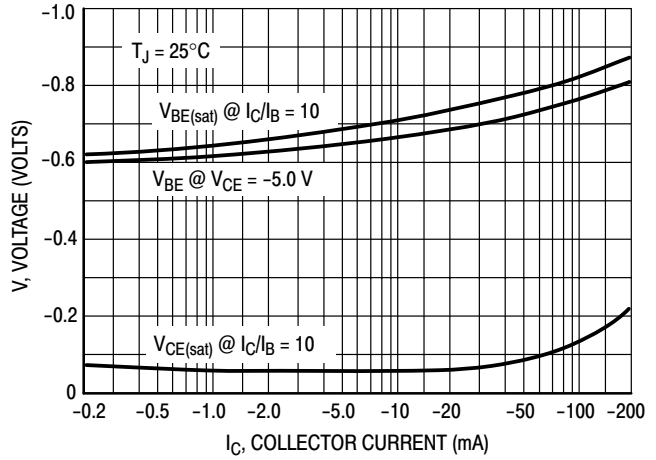


Figure 2. "On" Voltage

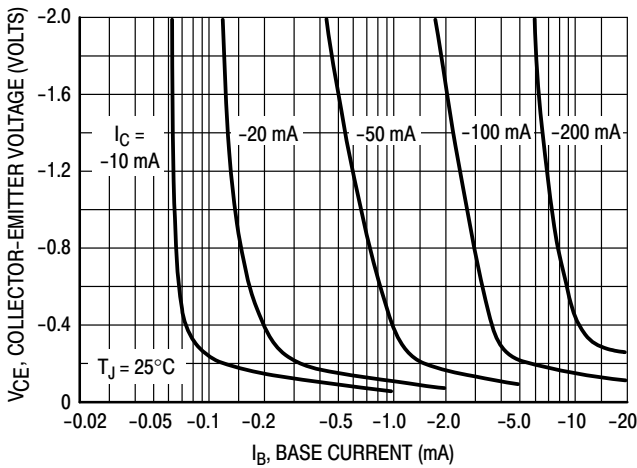


Figure 3. Collector Saturation Region

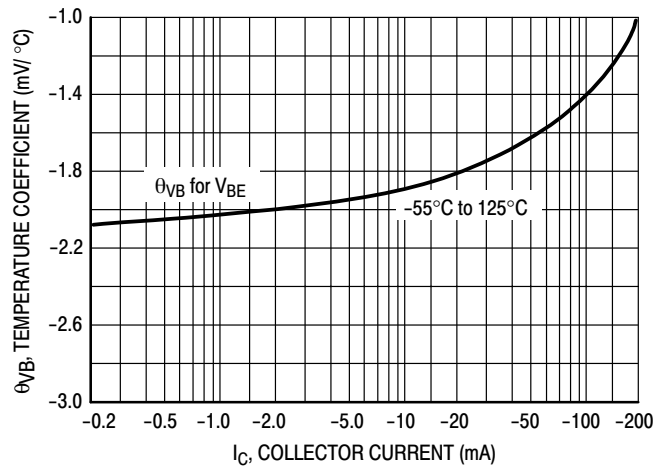


Figure 4. Base-Emitter Temperature Coefficient

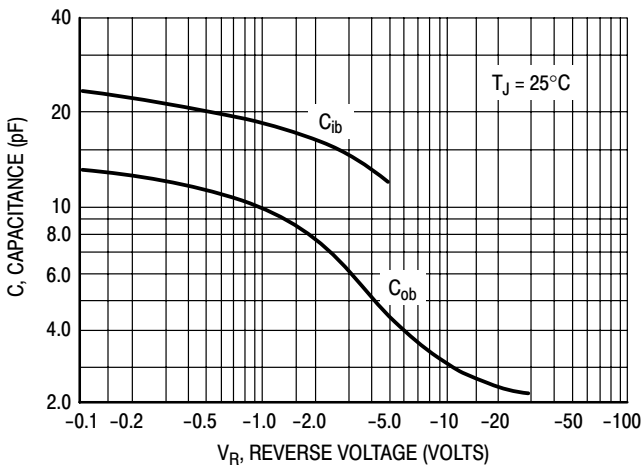


Figure 5. Capacitance

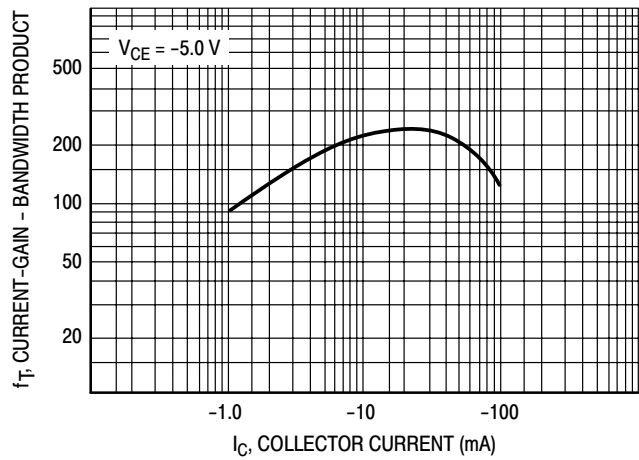


Figure 6. Current-Gain - Bandwidth Product

BC856BDW1T1, BC857BDW1T1 Series, BC858CDW1T1 Series

TYPICAL CHARACTERISTICS – BC857/BC858

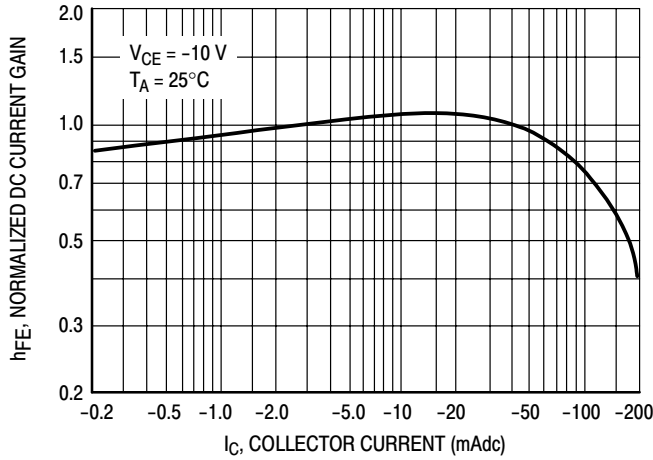


Figure 7. Normalized DC Current Gain

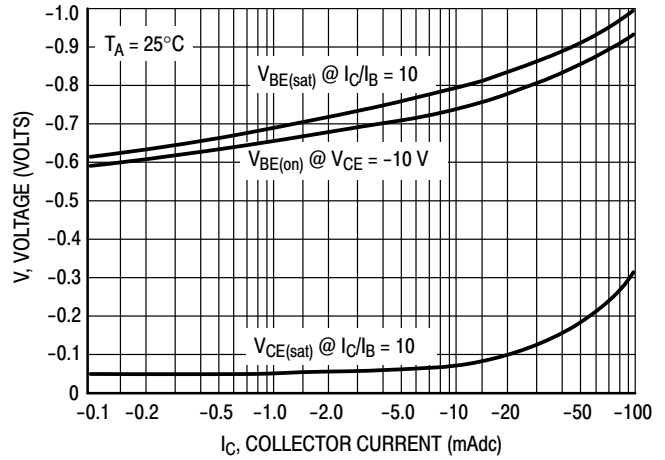


Figure 8. "Saturation" and "On" Voltages

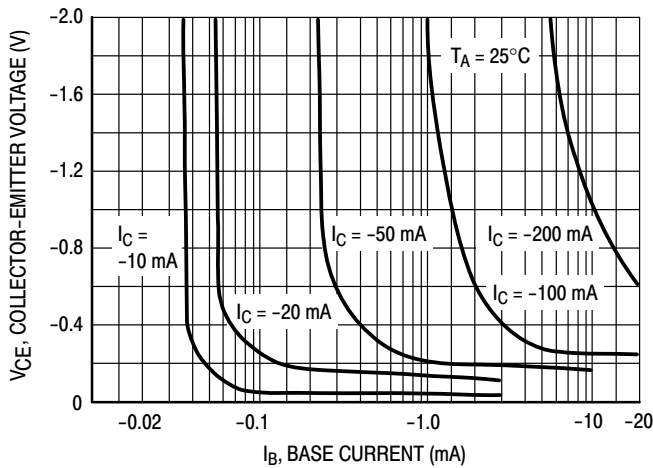


Figure 9. Collector Saturation Region

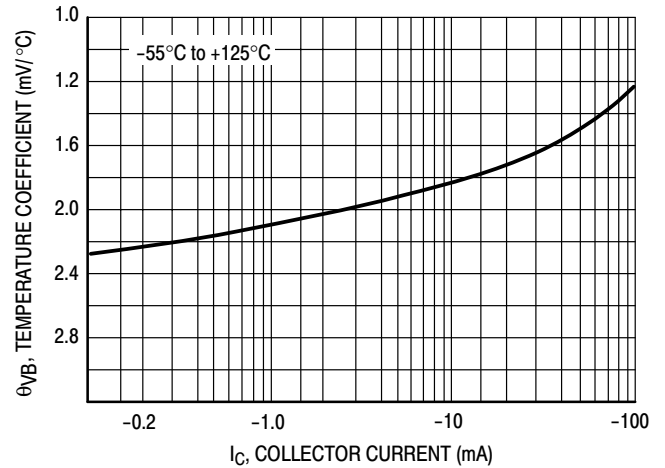


Figure 10. Base-Emitter Temperature Coefficient

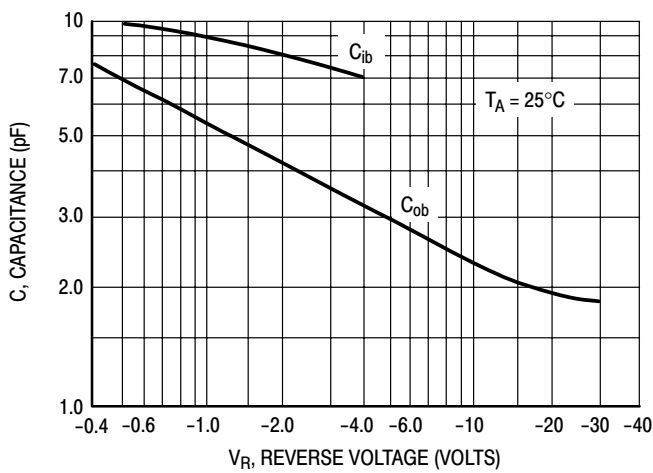


Figure 11. Capacitances

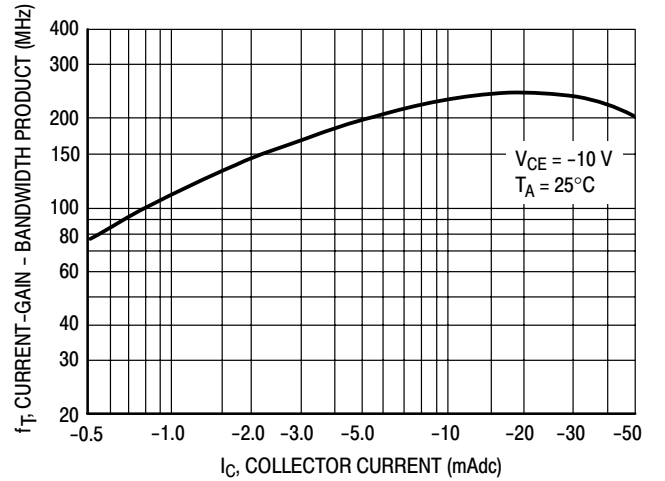


Figure 12. Current-Gain – Bandwidth Product

BC856BDW1T1, BC857BDW1T1 Series, BC858CDW1T1 Series

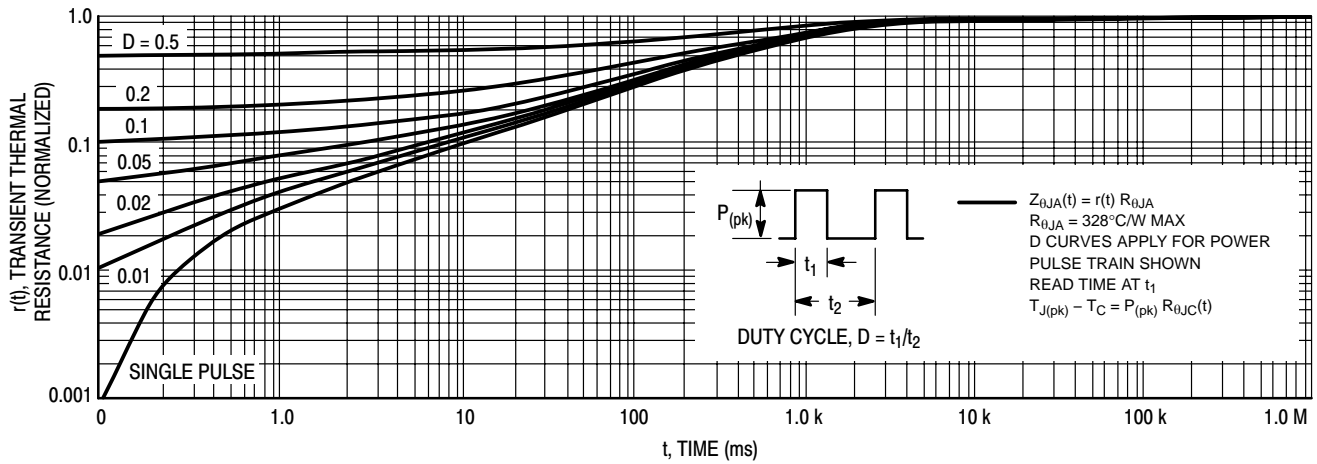


Figure 13. Thermal Response

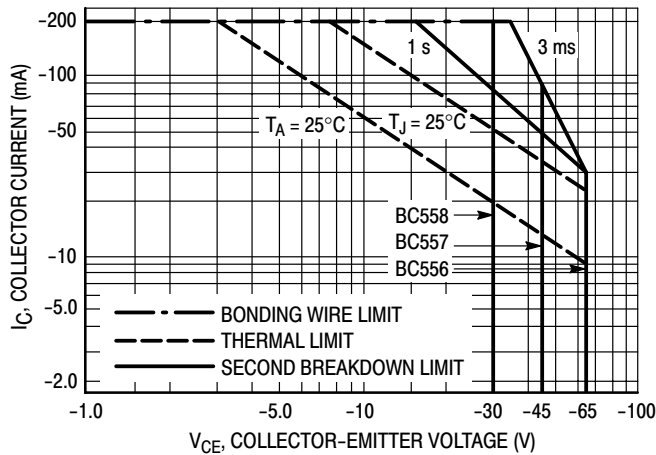


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

ORDERING INFORMATION

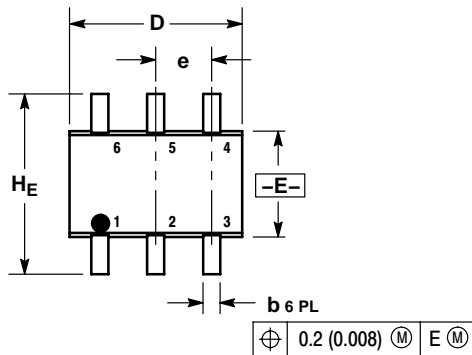
Device	Device Marking	Package	Shipping†
BC856BDW1T1	3B	SOT-363	3,000 / Tape & Reel
BC856BDW1T1G	3B	SOT-363 (Pb-Free)	
BC856BDW1T3	3B	SOT-363	10,000 / Tape & Reel
BC856BDW1T3G	3B	SOT-363 (Pb-Free)	
BC857BDW1T1	3F	SOT-363	3,000 / Tape & Reel
BC857BDW1T1G	3F	SOT-363 (Pb-Free)	
BC857CDW1T1	3G	SOT-363	3,000 / Tape & Reel
BC857CDW1T1G	3G	SOT-363 (Pb-Free)	
BC858CDW1T1	3L	SOT-363	3,000 / Tape & Reel
BC858CDW1T1G	3L	SOT-363 (Pb-Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BC856BDW1T1, BC857BDW1T1 Series, BC858CDW1T1 Series

PACKAGE DIMENSIONS

SC-88 (SOT-363)
CASE 419B-02
ISSUE V



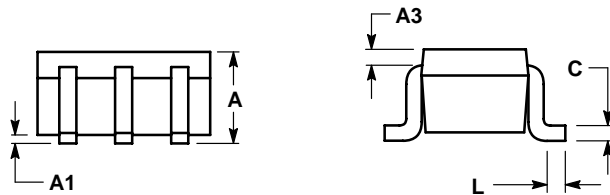
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

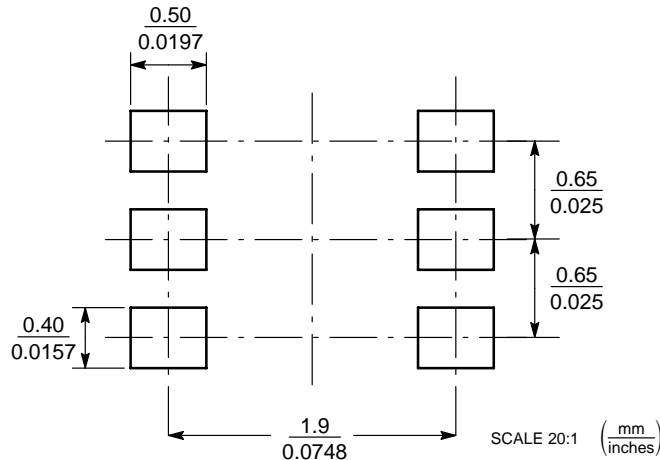
DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
c	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 1:

- PIN 1: EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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